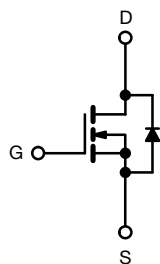
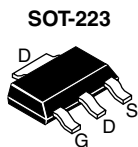


Power MOSFET



N-Channel MOSFET



RoHS
COMPLIANT
HALOGEN
FREE
Available

FEATURES

- Surface-mount
- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-223 package is designed for surface-mounting using vapor phase, infrared, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of greater than 1.25 W is possible in a typical surface mount application.

Marking code: FD

PRODUCT SUMMARY		
V _{DS} (V)	250	
R _{DS(on)} (Ω)	V _{GS} = 10 V	2.0
Q _g (Max.) (nC)	8.2	
Q _{gs} (nC)	1.8	
Q _{gd} (nC)	4.5	
Configuration	Single	

ORDERING INFORMATION	
Package	SOT-223
Lead (Pb)-free and halogen-free	SiHFL214TR-GE3 ^a
	IRFL214TRPbF-BE3 ^{a, b}
Lead (Pb)-free	IRFL214TRPbF ^a

Notes

- See device orientation
- “-BE3” denotes alternate manufacturing location

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-source voltage	V _{DS}		250	V
Gate-source voltage	V _{GS}		± 20	
Continuous drain current	V _{GS} at 10 V	T _C = 25 °C	0.79	A
		T _C = 100 °C	0.50	
Pulsed drain current ^a	I _{DM}		6.3	W/°C
Linear derating factor			0.025	
Linear derating factor (PCB mount) ^e			0.017	
Single pulse avalanche energy ^b	E _{AS}		50	mJ
Avalanche current ^a	I _{AR}		0.79	A
Repetitive avalanche energy ^a	E _{AR}		0.31	mJ
Maximum power dissipation	T _C = 25 °C		3.1	W
Maximum power dissipation (PCB mount) ^e	T _A = 25 °C		2.0	
Peak diode recovery dv/dt ^c	dV/dt		4.8	V/ns
Operating junction and storage temperature range	T _J , T _{stg}		-55 to +150	°C
Soldering recommendations (peak temperature) ^d	For 10 s		300	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V_{DS} = 50 V, starting T_J = 25 °C, L = 128 mH, R_g = 25 Ω, I_{AS} = 0.79 A (see fig. 12)
- I_{SD} ≤ 2.7 A, dI/dt ≤ 65 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C
- 1.6 mm from case
- When mounted on 1" square PCB (FR-4 or G-10 material)

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum junction-to-ambient (PCB mount) ^a	R_{thJA}	-	-	60	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	-	40	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

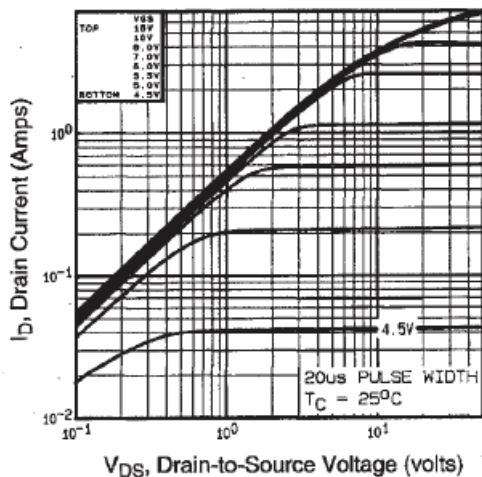
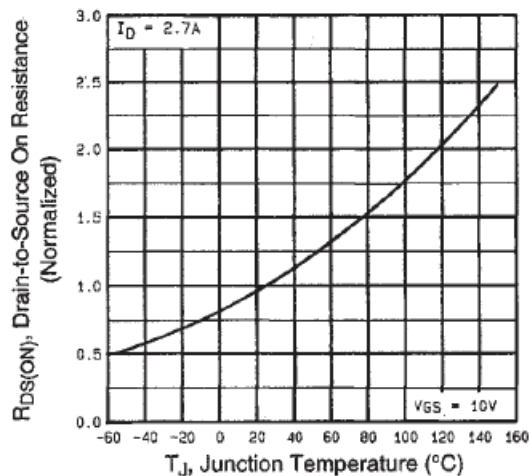
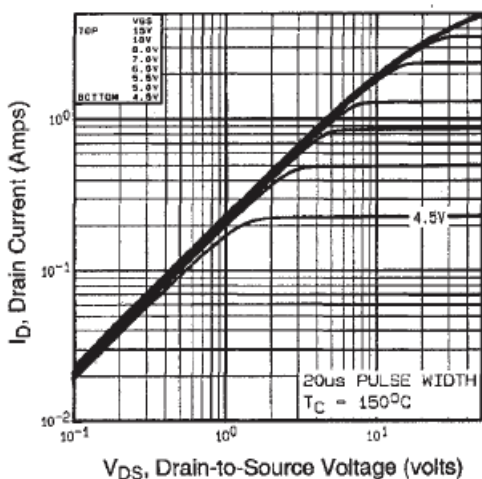
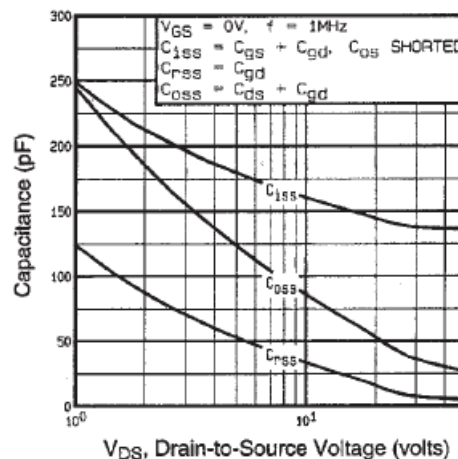
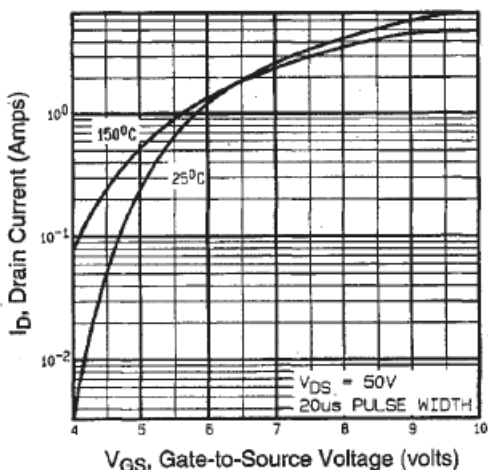
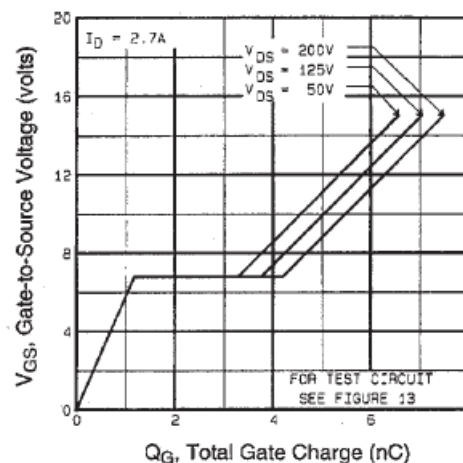
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

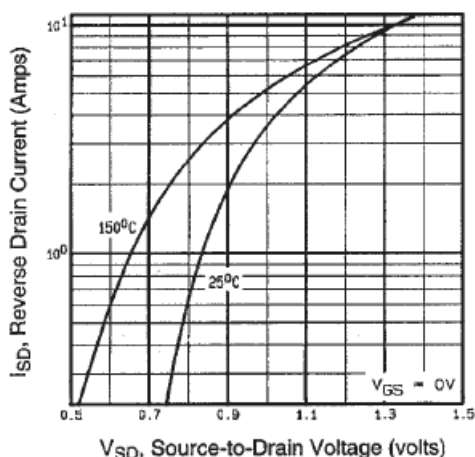
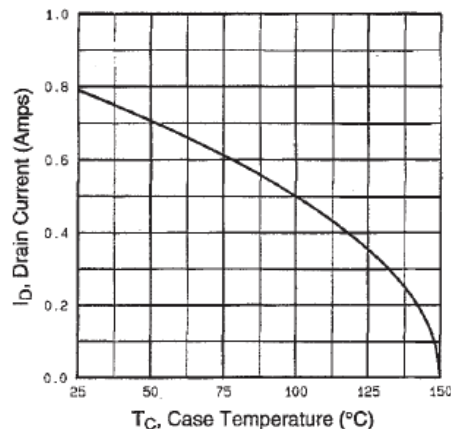
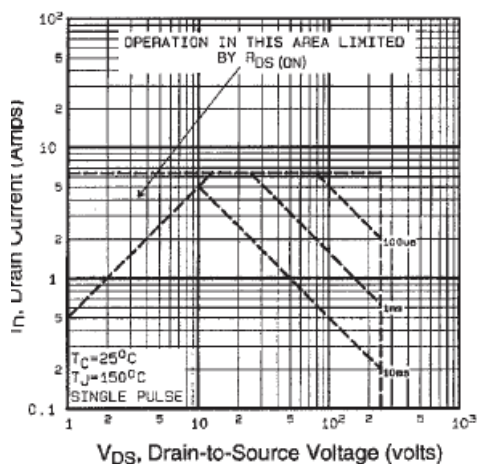
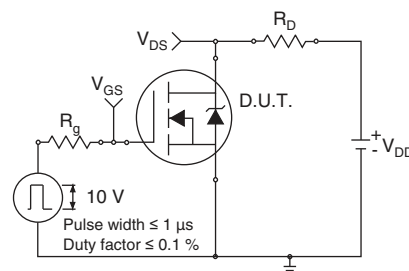
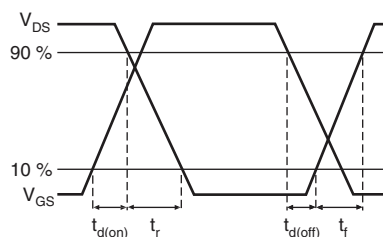
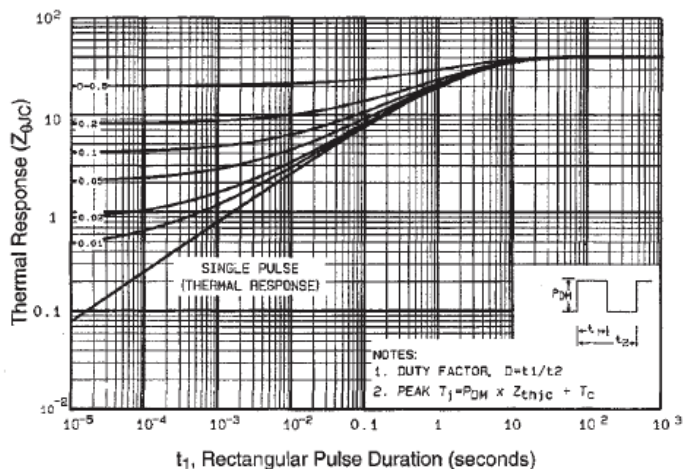
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		250	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.39	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 0.47 A ^b	-	-	2.0	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 0.47 A		0.50	-	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	140	-	pF
Output capacitance	C _{oss}			-	42	-	
Reverse transfer capacitance	C _{rss}			-	9.6	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 2.7 A, V _{DS} = 200 V, see fig. 6 and 13 ^b	-	-	8.2	nC
Gate-source charge	Q _{gs}			-	-	1.8	
Gate-drain charge	Q _{gd}			-	-	4.5	
Turn-on delay time	t _{d(on)}	V _{DD} = 125 V, I _D = 2.7 A, R _g = 24 Ω, R _D = 45 Ω, see fig. 10 ^b		-	7.0	-	ns
Rise time	t _r			-	7.6	-	
Turn-off delay time	t _{d(off)}			-	16	-	
Fall time	t _f			-	7.0	-	
Internal drain inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.0	-	nH
Internal source inductance	L _S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	0.79	A
Pulsed diode forward current ^a	I _{SM}			-	-	6.3	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 0.79 A, V _{GS} = 0 V ^b		-	-	2.0	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 2.7 A, dI/dt = 100 A/μs ^b		-	190	390	ns
Body diode reverse recovery charge	Q _{rr}			-	0.64	1.3	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

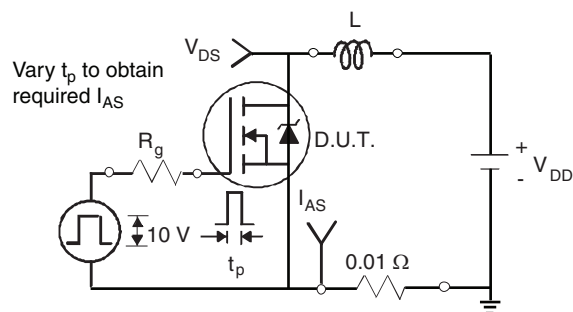
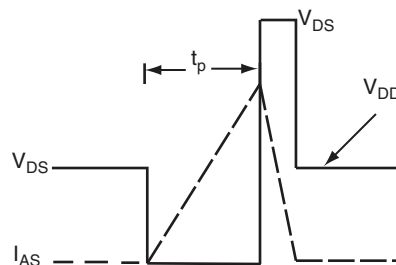
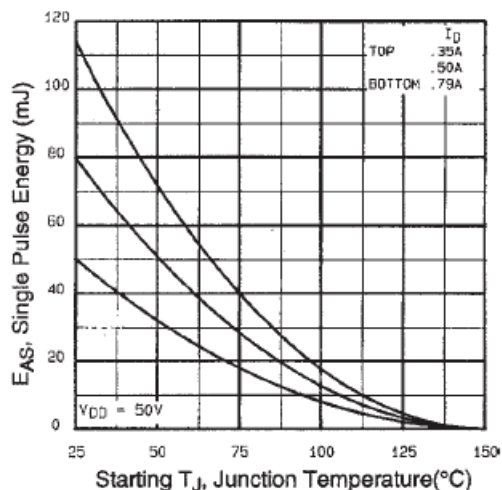
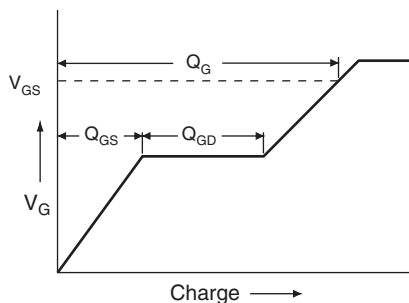
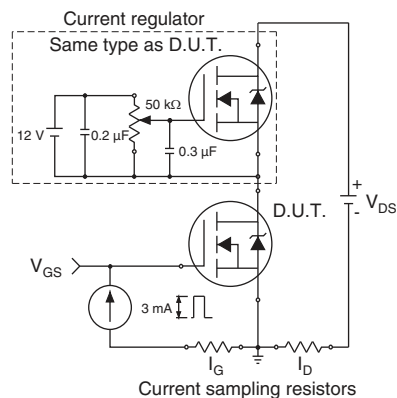
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

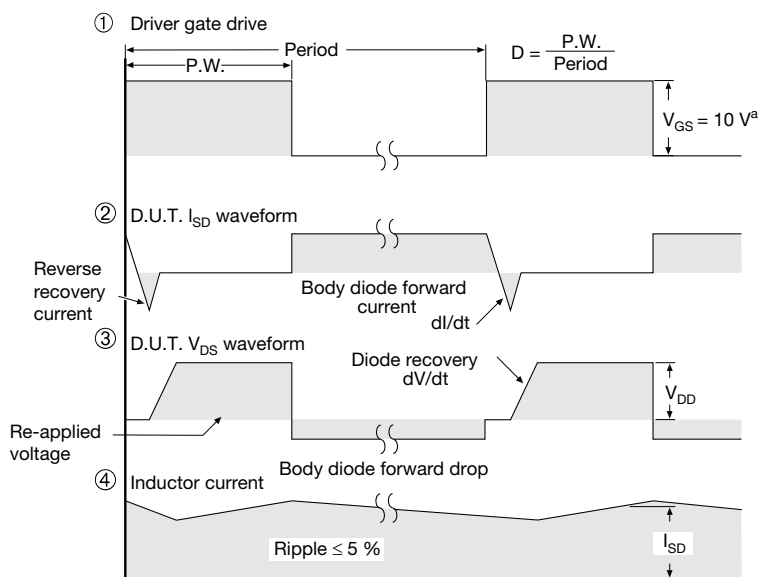
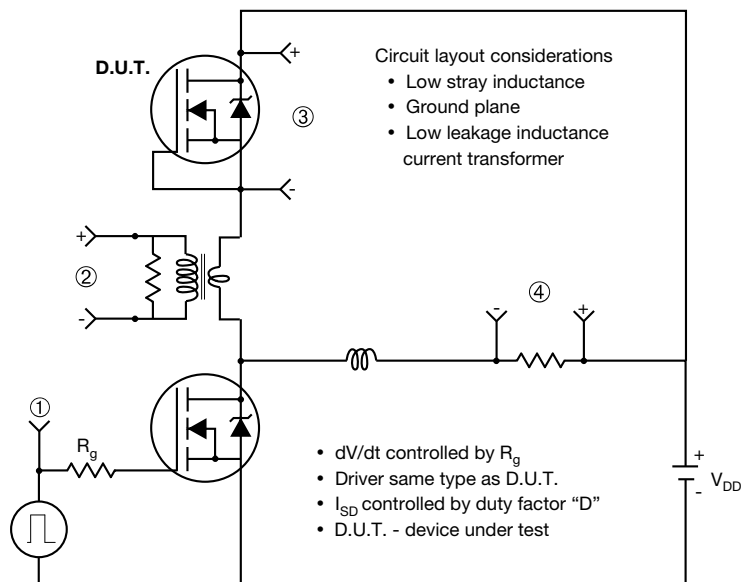
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case


Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Fig. 13a - Basic Gate Charge Waveform

Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



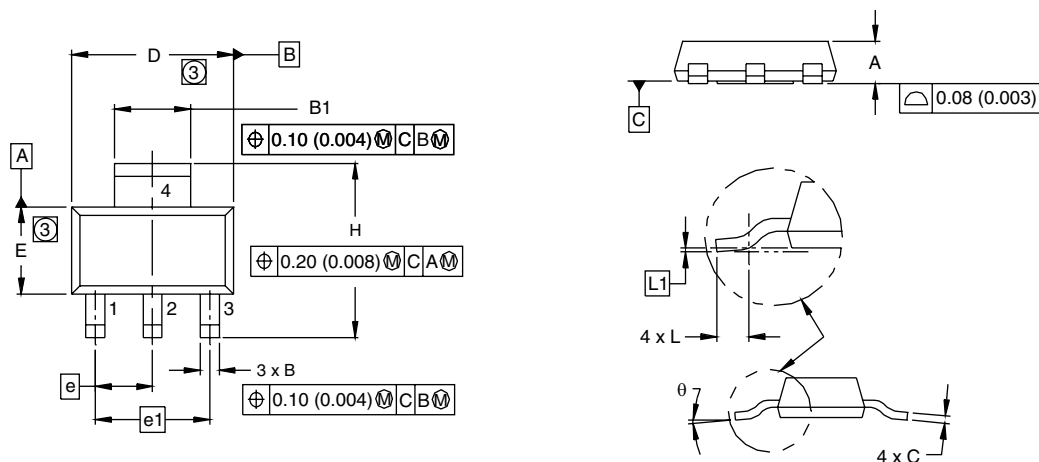
Note

a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig.14 - For N-Channel

Vishay Silconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silcon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91194.

SOT-223 (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10°	-	10°
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.



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